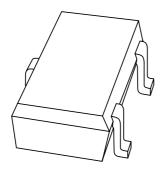
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# PMST5550; PMST5551 NPN high-voltage transistors

Product data sheet Supersedes data of 1997 May 20 1999 Apr 29



## **NPN** high-voltage transistors

PMST5550; PMST5551

#### **FEATURES**

• Low current (max. 300 mA)

• High voltage (max. 160 V).

#### **APPLICATIONS**

• Switching and amplification in high voltage applications such as telephony.

#### **DESCRIPTION**

NPN high-voltage transistor in a SOT323 plastic package. PNP complement: PMST5401.

#### **MARKING**

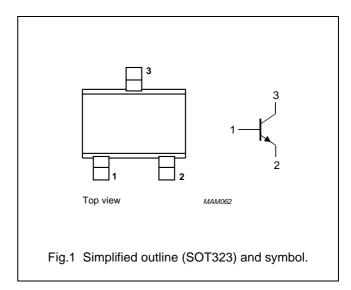
TYPE NUMBER	MARKING CODE(1)
PMST5550	*1F
PMST5551	*G3

#### Note

\* = - : Made in Hong Kong.
 \* = t : Made in Malaysia.

#### **PINNING**

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	PMST5550		_	160	V
	PMST5551		_	180	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	PMST5550		_	140	V
	PMST5551		_	160	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current (DC)		-	300	mA
I <sub>CM</sub>	peak collector current		_	600	mA
I <sub>BM</sub>	peak base current		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

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#### Note

1. Transistor mounted on an FR4 printed-circuit board.

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## NPN high-voltage transistors

PMST5550; PMST5551

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	625	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 100 V	_	100	nA
	PMST5550	I <sub>E</sub> = 0; V <sub>CB</sub> = 100 V; T <sub>amb</sub> = 100 °C	_	100	μΑ
	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 120 V	_	50	nA
	PMST5551	I <sub>E</sub> = 0; V <sub>CB</sub> = 120 V; T <sub>amb</sub> = 100 °C	_	50	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 4 V	_	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; (see Fig.2)			
	PMST5550	$I_C = 1 \text{ mA}$	60	_	
		$I_C = 10 \text{ mA}$	60	250	
		I <sub>C</sub> = 50 mA; note 1	20	_	
	DC current gain	V <sub>CE</sub> = 5 V; (see Fig.2)			
	PMST5551	$I_C = 1 \text{ mA}$	80	_	
		I <sub>C</sub> = 10 mA	80	250	
		I <sub>C</sub> = 50 mA; note 1	30	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	-	150	mV
	collector-emitter saturation voltage	$I_C = 50 \text{ mA}$ ; $I_B = 5 \text{ mA}$ ; note 1			
	PMST5550		_	250	mV
	PMST5551		_	200	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	_	1	V
	base-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$			
	PMST5550		_	1.2	V
	PMST5551		_	1	V
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	6	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = 0.5 \text{ V}$ ; $f = 1 \text{ MHz}$	_	30	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	100	300	MHz
F	noise figure	$I_C$ = 200 μA; $V_{CE}$ = 5 V; $R_S$ = 2 kΩ;			
	PMST5551	f = 10 Hz to 15.7 kHz	_	8	dB

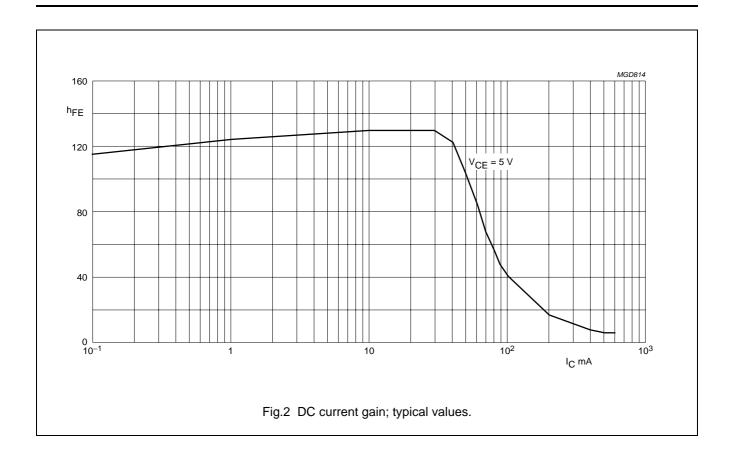
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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# NPN high-voltage transistors

# PMST5550; PMST5551



## NPN high-voltage transistors

PMST5550; PMST5551

**EUROPEAN** 

**PROJECTION** 

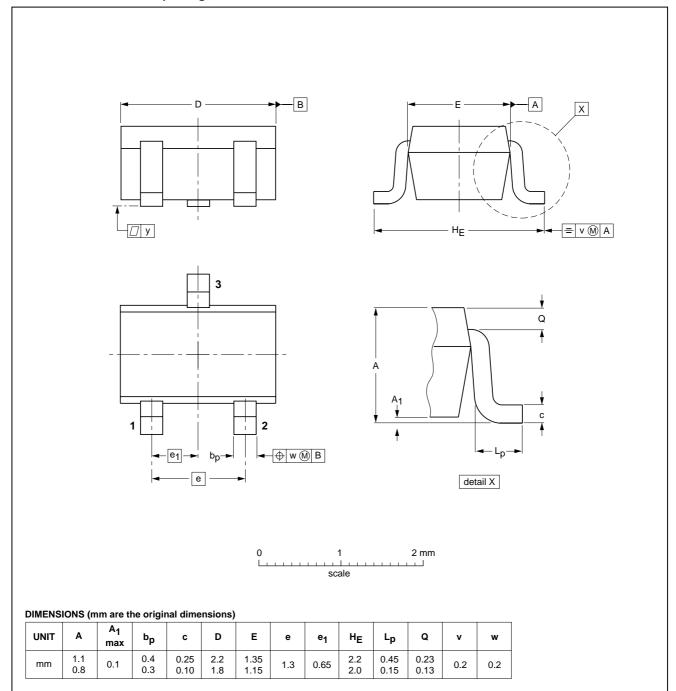
ISSUE DATE

97-02-28

#### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

**SOT323** 



**REFERENCES** 

EIAJ

SC-70

**JEDEC** 

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IEC

OUTLINE

VERSION

SOT323

### **NPN** high-voltage transistors

PMST5550; PMST5551

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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